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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Complete If Known			
		Application Number	10/780,143		
		Filing Date	February 17, 2004		
		First Named Inventor	Alexander Barr et al		
		Group Art Unit	2811		
Sheet	1	of	1	Examiner Name	
				Attorney Docket Number	SC13265TP

U. S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. 1	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			

FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Cite No. 1	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Office ³	Number ⁴	Kind Code ² (if known)				
	BA		WO 02/45156		Mark Armstrong et al	06-06-2002		

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁷
	BB	M. SHIMA et al - "<100> Channel Strained - SiGe p-MOSFET with Enhanced Hole Mobility and Lower Parasitic Resistance" (2002 Symposium on VLSI Technology Digest of Technical Papers, pg 94-95	

Examiner Signature		Date Considered	October 4 2005
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation, if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English Language Translation is attached.

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Complete if Known	
		Application Number	101780143
		Filing Date	FEBRUARY 17, 2004
		First Named Inventor	Alexander L. Barr et al.
		Group Art Unit	2823
		Examiner Name	W. DAVID COLEMAN
Sheet	1	of	1
		Attorney Docket Number	SC13265TP

U. S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number -Kind Code ² (if known)			
	AA	US -6,429,061 B1	08-06-2002	RIM	
		US -			
		US -			
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		US -			

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³	Number ⁴ Kind Code ² (if known)				
	AB	PCT	WO02/080241 A1	10-10-202	IBM		

NON PATENT LITERATURE DOCUMENTS			
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	AC	LANGDO et al., "Preparation of Novel SiGe-Free Strained Si on Insulator Substrates," AMBERWAVE SYSTEMS CORP., SALEM, NH, 2 pgs.	
	AD	MATSUMOTO et al., "Novel SOI Wafer Engineering Using Low Stress and High Mobility CMOSFET with <100>-Channel for Embedded RF/Analog Applications," IEEE, pp. 663-666 (2002).	
	AE	SAYAMA et al., "Effect of <100> Channel Direction for High Performance SCE Immune pMOSFET with Less Than 0.15µm Gate Length," IEEE, 4 pgs., (1999).	
	AF	AOKI et al., "Optimum Crystallographic Orientation of Submicrometer CMOS Devices Operated at Low Temperatures," IEEE TRANSACTIONS ON ELECTRON DEVICES, VOL. ED-34, NO. 1, JANUARY 1987, pp. 52-57.	

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